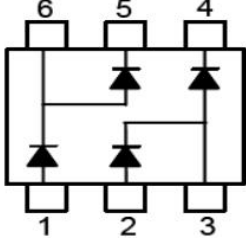


SOT-23-6L Switching Diode 开关二极管
Internal Configuration& Device Marking 内部结构与产品打标

Pin 管脚		
Mark 打标	B34	

Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Non-Repetitive Peak Reverse Voltages 不重复反向峰值电压	V_{RRM}	350	V
DC Reverse Voltage 直流反向电压	V_{RM}	300	V
RMS Reverse Voltage 反向电压均方根值	V_{RMS}	212	V
Forward Work Current 正向工作电流	$I_F(I_O)$	225	mA
Peak Forward Current 正向峰值电流	I_{FRM}	625	mA
Non-Repetitive Peak Surge Current 不重复峰值浪涌电流	I_{FSM}	1@t=1S	A
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	350	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	358	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

Electrical Characteristics 电特性

 (TA=25 $^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 25 $^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=150\mu A$)	$V_{(BR)}$	350	—	—	V
Reverse Leakage Current($V_R=240V$) 反向漏电流($V_R=240V, T_J=150^{\circ}C$)	I_R	—	20 0.5	100 100	nA μA
Forward Voltage($I_F=100mA$) 正向电压($I_F=200mA$)	V_F	—	0.95 1	1 1.25	V
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_D	—	2	5	pF
Reverse Recovery Time 反向恢复时间 $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega, I_F = 10 mA, V_R = 6V$	T_{rr}	—	—	50	nS

■ Typical Characteristic Curve 典型特性曲线

Fig.1 Power Derating Curve

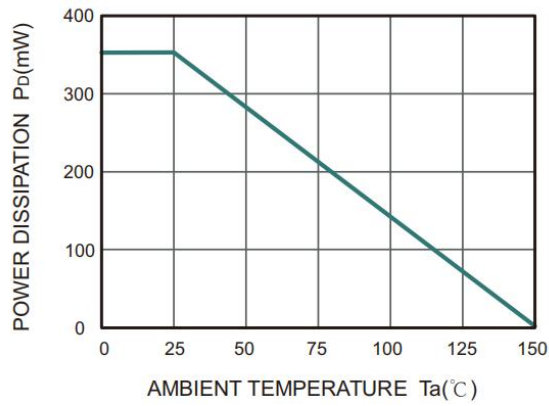


Fig.2 Reverse Characteristics

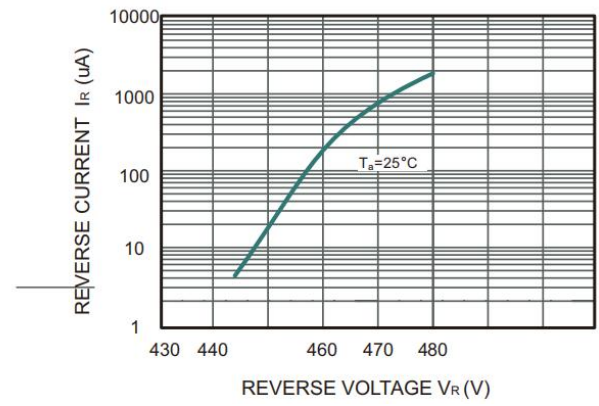


Fig.3 Forward Characteristics

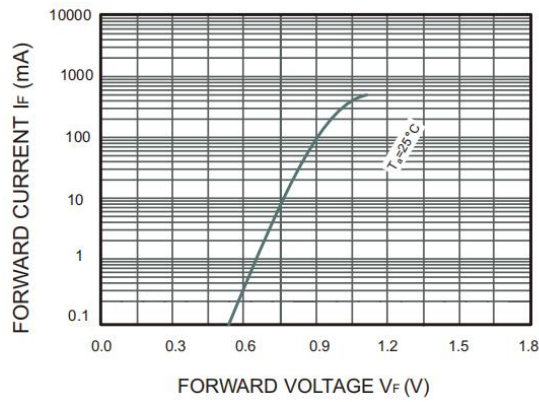


Fig.4 Capacitance Characteristics

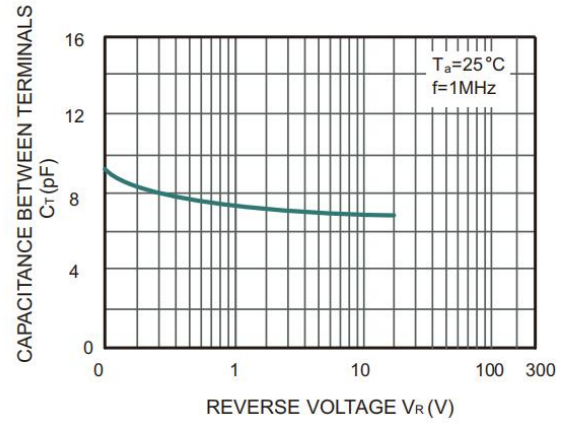
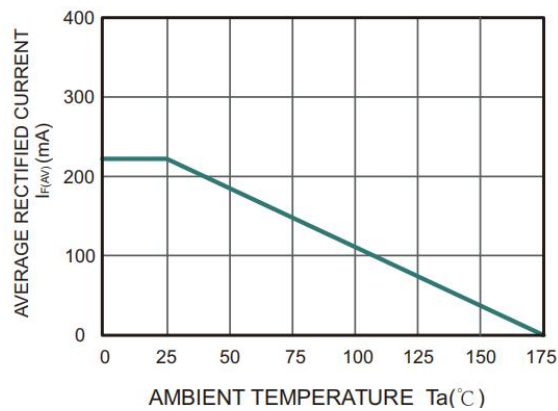
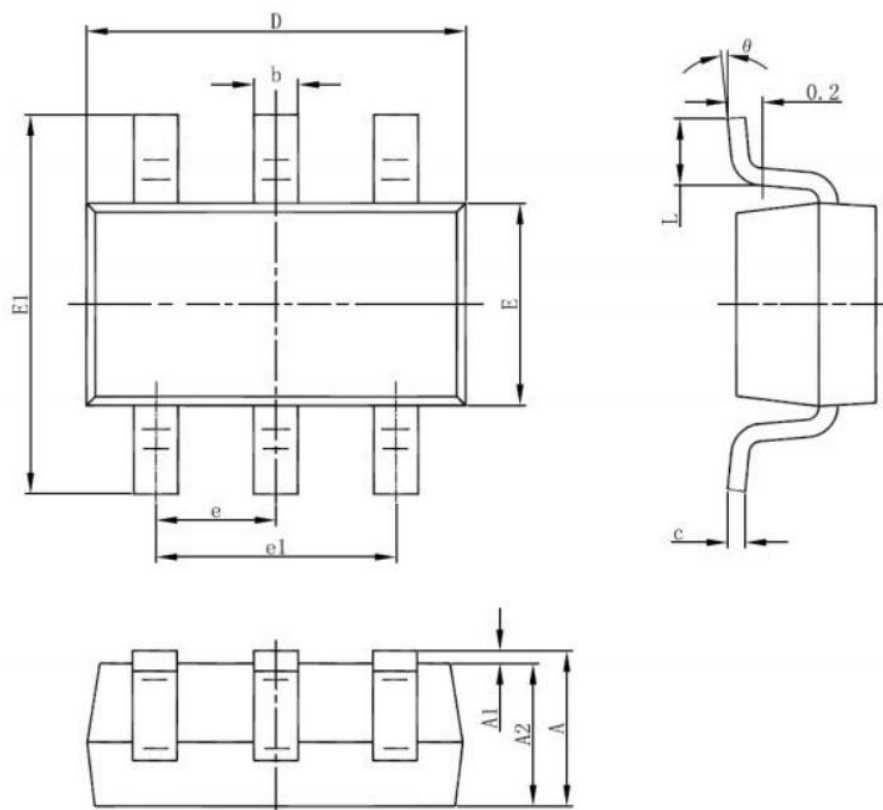


Fig.5 Semiconductor Intrinsic Property



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.450	0.650	0.018	0.026
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°